

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None	
	5.0	Overall Thickness	431.80 +/- 13.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	7.0	Bow	<80.00 μ m	ADE to ASTM F534, 20%
	8.0	Warp	<80.00 μ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	390.00 +/- 10.00 μ m	ADE, 100%
	14.0	Handle Doping Type	Any	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	>0.005 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide and lasermark	Guaranteed by Process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle Wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	23.0	Nominal Thickness	10.00 +/- 1.00 μ m	FTIR, 100% 9-Pt (note3)
	24.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	25.0	Device Doping Type	Any	Wafer Vendor
	26.0	Device Dopant	Any	Wafer Vendor
	27.0	Device Resistivity	>0.005 Ohmcm	Wafer Vendor
BuriedOxide2	28.0	Oxide 2 Type	Thermal	
	29.0	Oxide 2 Thickness	5,000.00 +/- 500.00 A	Nanospec centre point measurement, 4%
	30.0	Oxide 2 formed on	Device 2 wafer	Guaranteed by Process
DeviceSilicon2	31.0	Device 2 Growth Method	CZ	Wafer Vendor
	32.0	Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	33.0	Device 2 Nominal Thickness	30.00 +/- 2.00 μ m	ADE Single Point, 100%
	34.0	Distance to Device 2 edge from wafer edge	<= 3mm	Guaranteed by Process

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DeviceSilicon2	35.0	Device 2 DopingType	Any	Wafer Vendor
	36.0	Device 2 Dopant	Any	Wafer Vendor
	37.0	Device 2 Resistivity	<0.001 Ohmcm	Wafer Vendor
	38.0	Device 2 Field Oxidation	3,000.00 +/- 300.00 A	Nanospec centre point, 4%
DeviceSilicon	39.0	VOIDS	none	Wafer Vendor
	40.0	Scratches	0	Bright Light, 100% (note 2)
	41.0	Haze	none	Bright Light, 100% (note 2)

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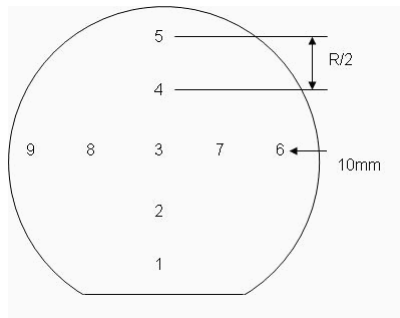
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information